

FOR PTO-1449 (Modified)  
**LIST OF PATENTS AND PUBLICATIONS FOR  
 APPLICANTS INFORMATION DISCLOSURE  
 STATEMENT**

(Use several sheets if necessary)

ATTY. DOCKET NO.

3521.150

SERIAL NO.

09/941,817

APPLICANT

SOMIT TALWAR, et al.

COPY OF PAPERS  
 ORIGINALLY FILED

FILING DATE

August 29, 2001

GROUP

2812

REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER								DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
dt	A	6	2	7	4	4	8	8		8-14-01	Talwar, et al.	438	655	4-12-00

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER								DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
														YES	NO

OTHER

ART (Including Author, Title, Date, Pertinent Pages, Etc.)

dt	B	Somit Talwar, Gaurav Verma, Kurt Weiner, <i>Ultra-Shallow, Abrupt, and Highly-Activated Junctions by Low-Energy Ion Implantation and Laser Annealing</i> , IEEE, 1999, pp. 1171-1174
dt	C	P.S. Peercy, J. Y. Tsao, S. R. Stiffler and Michael O. Thompson, <i>Explosive Crystallization in Amorphous Si Initiated by Long Pulse Width Laser Irradiation</i> , Appl. Phys. Lett. 52 (3), January 18, 1988, pp 203-205

EXAMINER

DATE CONSIDERED

12-08-02

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.